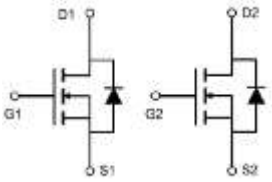
HMN3050AD5

30V_{DS}/±20V_{GS} Dual N-Channel Mode MOSFET

Features

- V_{DS}=30V,I_D=50A
- $R_{DS(ON)}$=5.5mΩ（TYP.）V_{GS}=10V
- $R_{DS(ON)}$=12mΩ（TYP.）V_{GS}=4.5V
- Reliable and Rugged
- Low Gate Charge and On-Resistance
- High Current Capability



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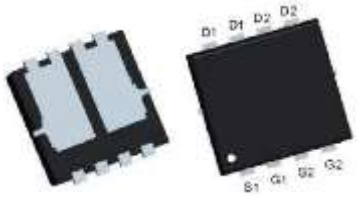


Applications

- DC/DC Converters in Computing, Servers, and POL
- Isolated DC/DC Converters in Telecom and Industrial

Ordering Information

Device	package	Device Marking	Package Qty.
HMN3050AD5	**PDFN5*6**	**	**5000/PCS**

Absolute Maximum Ratings (T$_C$=25℃,unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage (V_{GS}=0V)	V_{DS}	30	V
Gate-Source Voltage (V_{GS}=0V,static)	V_{GS}	±20	V
Continuous Drain Current (T_C=25℃)	I_D	50	A
Continuous Drain Current (T_C=100℃)		30	A
Pulesd Drain Current	I_{DM}	220	A
Single Pulsed Avalanche Energy	E_{AS}	45	mJ
Maximum Power Dissipation (T_C =25℃)	P_D	36	W
Operating,Storage Temperature Range	T_J,T_{STG}	-55~150	℃

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	-	2.72	-	℃/ W
Thermal Resistance,Junction-to-Ambient	$R_{\theta JA}$	-	-	-	℃/ W

Electrical Characteristics

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V,I_D=250μA	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V	-	-	1	μA
Gate -Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS},I_D=250μA	1.3	1.8	2.3	V
Drain-Source On-stage Resistance	$R_{DS(ON)}$	V_{GS}=10V,I_D=12A	-	4.2	5.5	mΩ
		V_{GS}=4.5V,I_D=10A	-	7.5	12	
Body Diode Forward Voltage	V_{SD}	V_{GS}=0V,I_{SD}=1A	-	0.7	1	V

Dynamic Characteristics

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	V_{DS}=15V	-	1614	-	pF
Output capacitance	C_{oss}	V_{GS}=0V	-	245	-	
Reverse transfer capacitance	C_{rss}	f=1MHz	-	215	-	
Gate Resistance	R_g	f=1MHz	-	1.9	-	Ω
Total Gate Charge	Q_g	V_{DS}=15V	-	33.7	-	nC
Gate Source Charge	Q_{gs}	V_{GS}=10V	-	8.5	-	
Gate Drain Charge	Q_{gd}	I_D=12A	-	7.5	-	
Turn-on delay Time	$t_{d(on)}$	V_{GS}=10V	-	7.5	-	ns
Rise time	t_r	V_{DS}=15V	-	14.5	-	
Turn-off delay Time	$t_{d(off)}$	R_L=0.75Ω	-	35.2	-	
Fall time	t_f	R_G=3Ω	-	9.6	-	
Reverse Recovery Time	t_{rr}	V_{GS}=0V,I_{SD}=12A	-	-	-	ns
Reverse Recovery Charge	Q_{rr}	d_i/d_t=500A/μs	-	-	-	nC

Electrical Characteristics Diagrames

Figure 1. On-Regin Characteristics

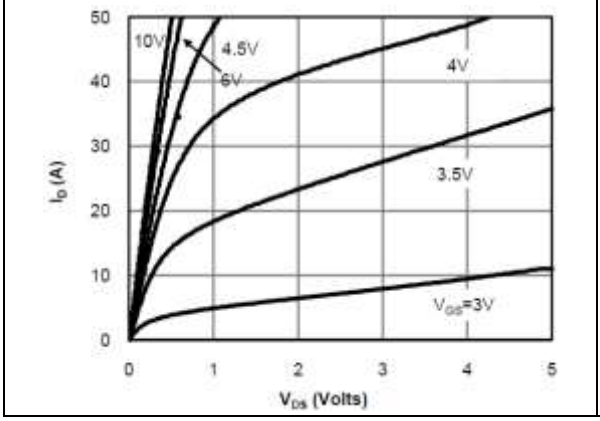


Figure 2. Transfer Characteristics

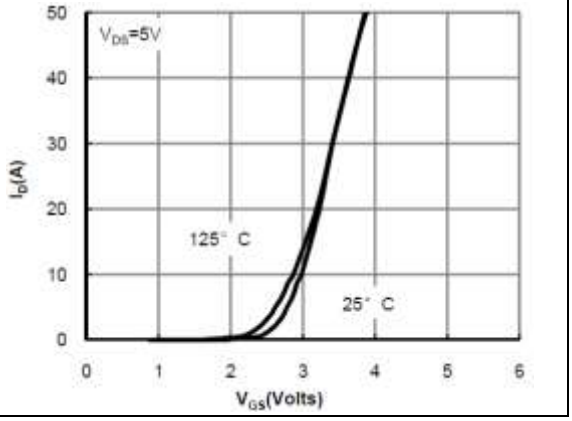


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

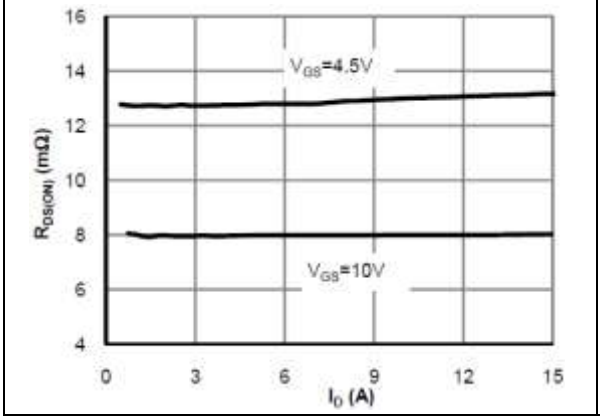


Figure 4. On-Resistance vs. Junction Temperature

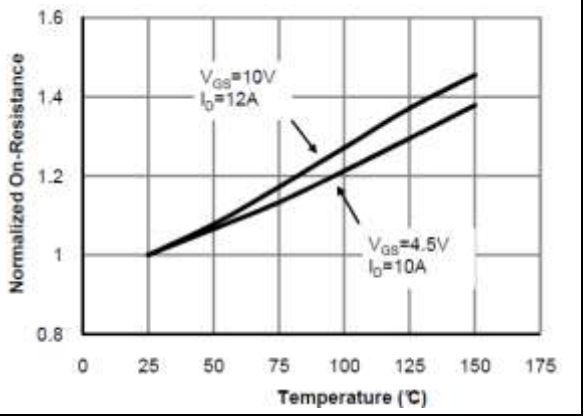


Figure 5. On-Resistance vs. Gate-Source Voltage

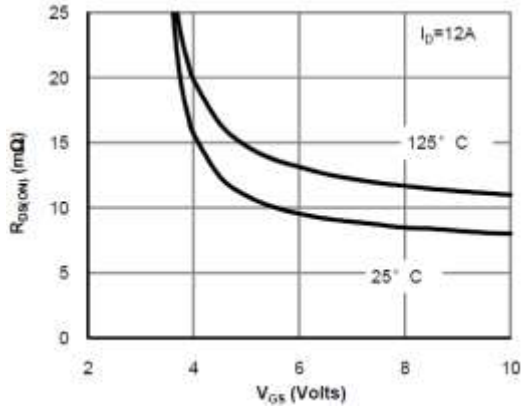


Figure 6. Body-Diode Characteristics

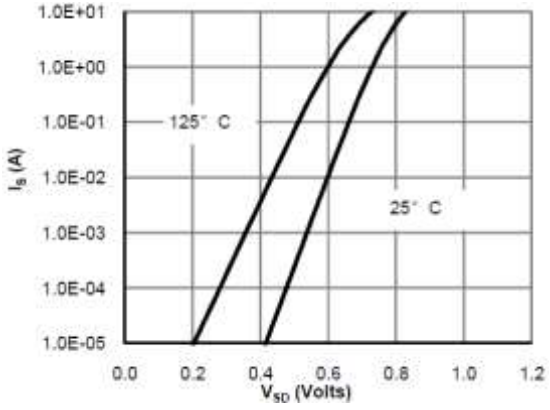


Figure 7. Gate-Charge Characteristics

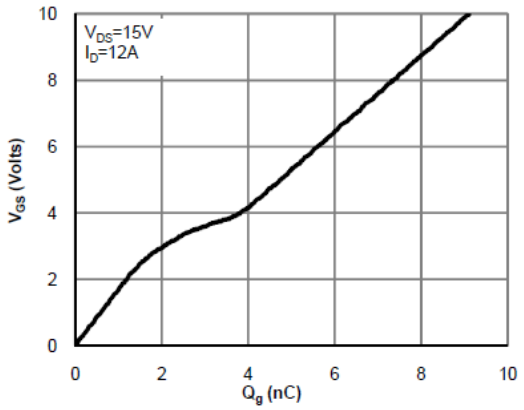


Figure 8. Capacitance Characteristics

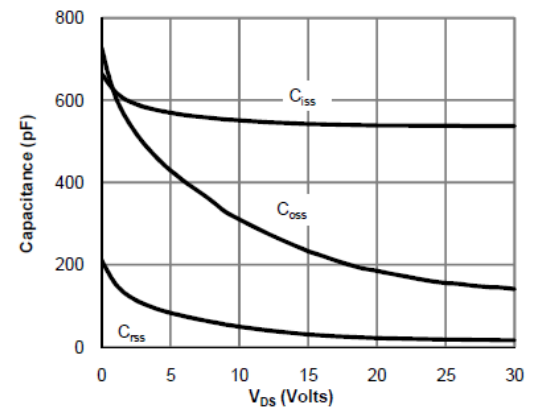


Figure 9. Maximum Forward Biased Safe Operating Area

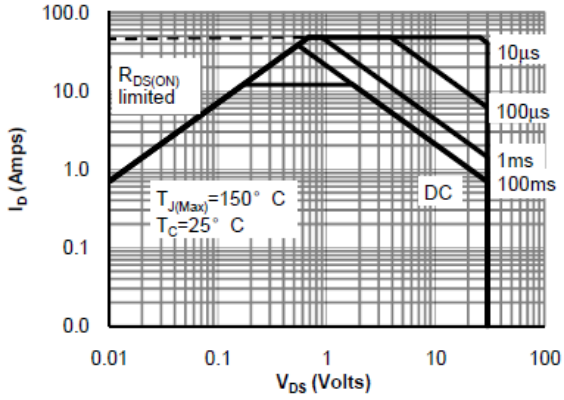


Figure 10. Single Pulse Power Rating Junction-to-Case

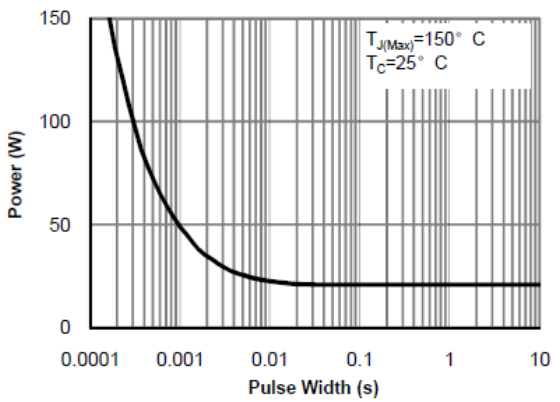
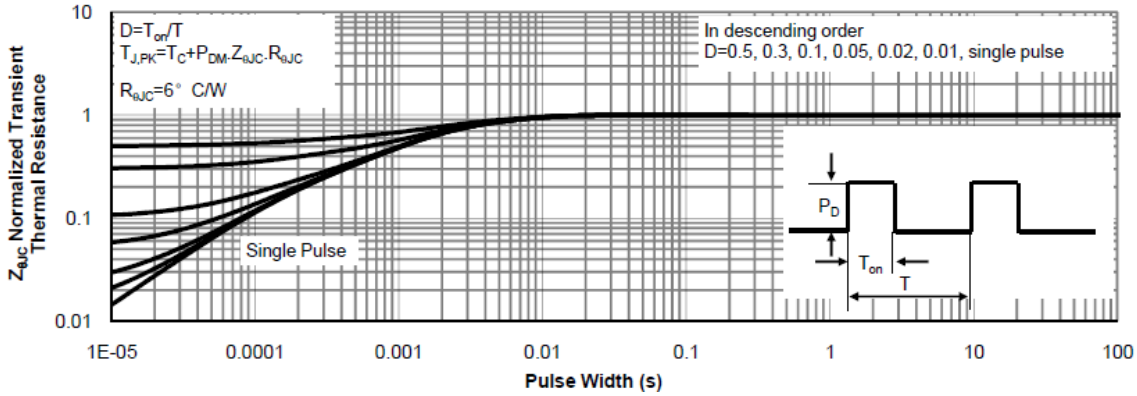
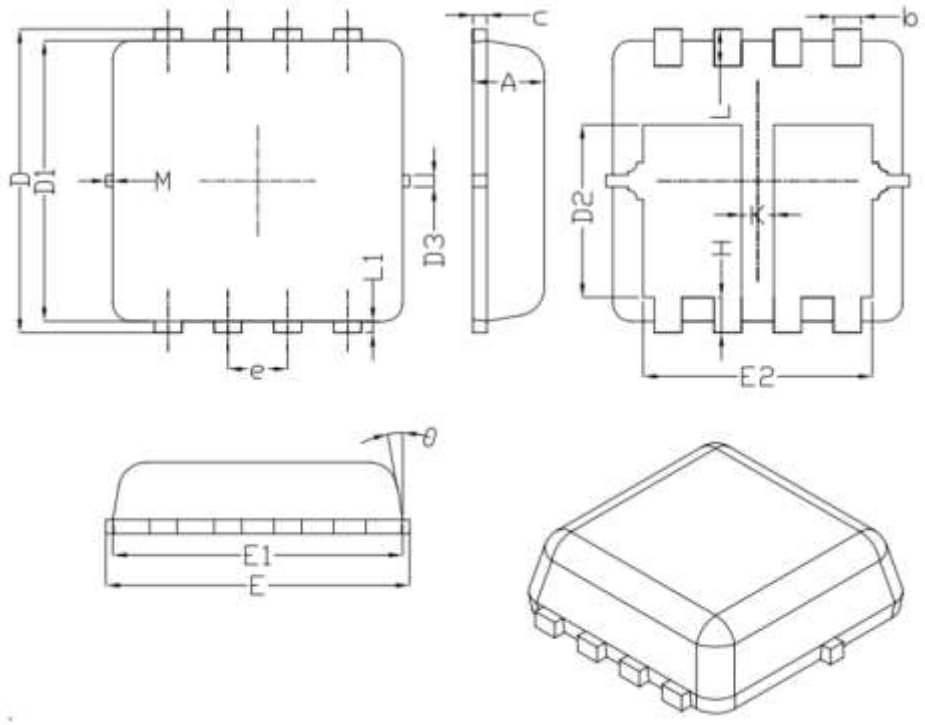


Figure 11. Normalized Maximum Transient Thermal Impedance



Physical Dimensions

PDFN5*6



符号	尺寸（mm）			符号	尺寸（mm）		
	最小值	典型值	最大值		最小值	典型值	最大值
A	0.90	1.00	1.10	E1	5.70	5.75	5.80
b	0.33	0.41	0.51	E2	3.38	3.58	3.78
c	0.20	0.25	0.30	H	0.41	0.51	0.61
D	4.80	4.90	5.00	K	1.10	-	-
D1	3.61	3.81	3.96	L	0.51	0.61	0.71
e	1.27BSC			L1	0.06	0.13	0.20
E	5.90	6.00	6.10	θ	0°	-	12°